PROCESS CPD18

Ultra Fast Rectifier

8 Amp Glass Passivated Rectifier Chip

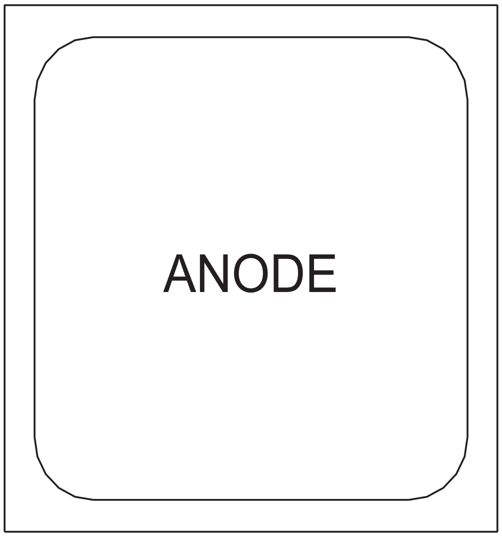
Central Semiconductor Corp.

www.DataSheet4U.com

PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	100 x 100 MILS
Die Thickness	14 MILS
Anode Bonding Pad Area	78 x 78 MILS
Top Side Metalization	Ni/Au - 5,000Å/2,000Å
Back Side Metalization	Ni/Au - 5,000Å/2,000Å

GEOMETRY



BACKSIDE CATHODE

R0

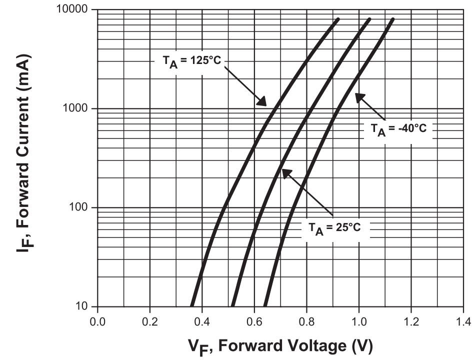
GROSS DIE PER 4 INCH WAFER
1,170

PRINCIPAL DEVICE TYPES
1N5807 thru 1N5811
UES1301 thru UES1306
UES1401 thru UES1403
CUDD8-02 Series

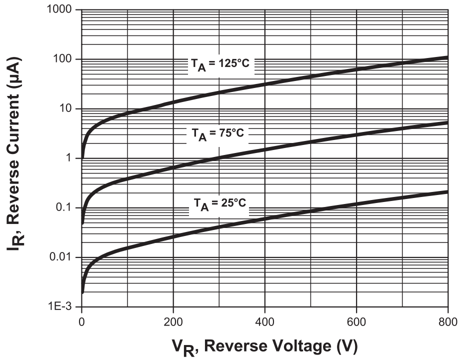
PROCESS CPD18

Typical Electrical Characteristics

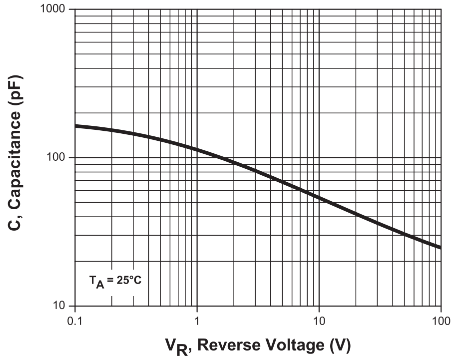
Forward Voltage



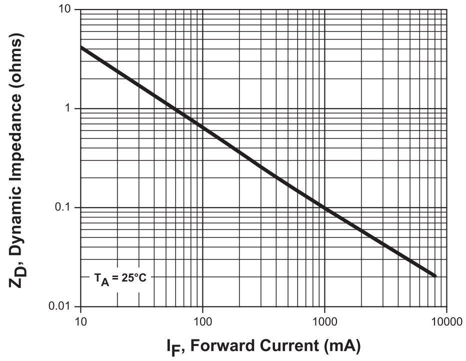
Leakage Current



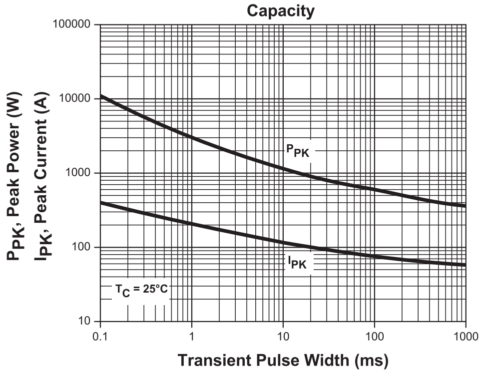
Capacitance



Forward Dynamic Impedance



Transient Peak Power and Peak Current Capacity



Normalized Power Derating